

MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV

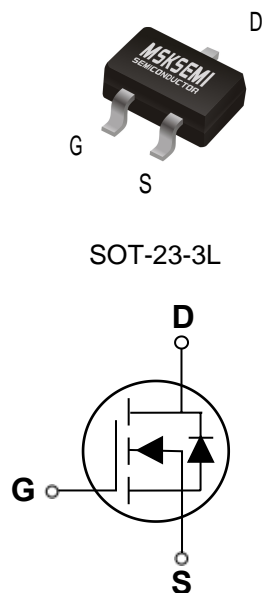


GDT



PLED

Product data sheet



Features

- 100V, 1.3A , $R_{DS(ON)}=500m\Omega$ @ $V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications

BVDSS	RDSON	ID
100V	500m Ω	1.3A

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain- Source Voltage	100	V
V_{GS}	Gate- Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^\circ\text{C}$)	1.3	A
	Drain Current – Continuous ($T_A=70^\circ\text{C}$)	1.12	A
I_{DM}	Drain Current – Pulsed ¹	5.6	A
P_D	Power Dissipation ($T_A=25^\circ\text{C}$)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ\text{C}/\text{W}$

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain- Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to $25^\circ C$, $I_D=1mA$	---	0.09	---	V/ $^\circ C$
I_{DSS}	Drain- Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$, $T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=125^\circ C$	---	---	10	μA
I_{GSS}	Gate- Source Leakage Current	$V_{GS}= \pm 20V$, $V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain- Source On- Resistance	$V_{GS}=10V$, $I_D=1A$	---	500	600	$m\Omega$
		$V_{GS}=4.5V$, $I_D=0.5A$	---	550	700	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	mV/ $^\circ C$
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=1A$	---	2.3	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2, 3}	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=1A$	---	9	---	nC
Q_{gs}	Gate-Source Charge ^{2, 3}		---	2.3	---	
Q_{gd}	Gate-Drain Charge ^{2, 3}		---	1.1	---	
$T_{d(on)}$	Turn-On Delay Time ^{2, 3}	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=1A$	---	5.2	---	ns
T_r	Rise Time ^{2, 3}		---	6.8	---	
$T_{d(off)}$	Turn-Off Delay Time ^{2, 3}		---	14.5	---	
T_f	Fall Time ^{2, 3}		---	2.1	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $F=1MHz$	---	492	---	pF
C_{oss}	Output Capacitance		---	27	---	
C_{rss}	Reverse Transfer Capacitance		---	15	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	13	A
I_{SM}	Pulsed Source Current		---	---	2.6	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ C$	---	---	1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

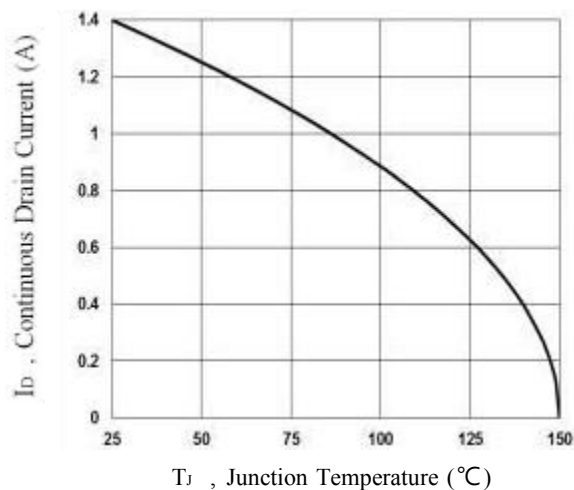


Fig. 1 Continuous Drain Current vs. T_J

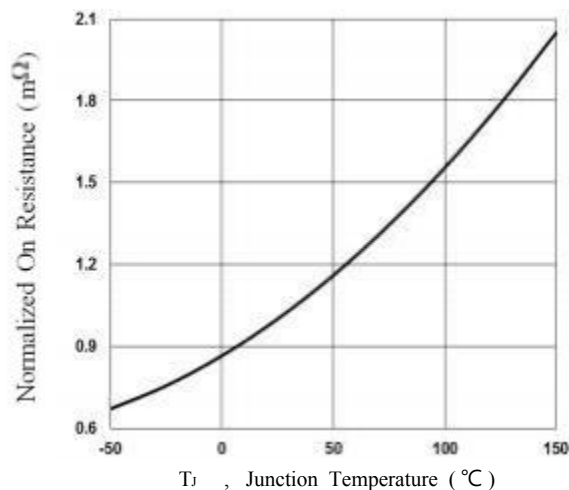


Fig. 2 Normalized $R_{DS(on)}$ vs. T_J

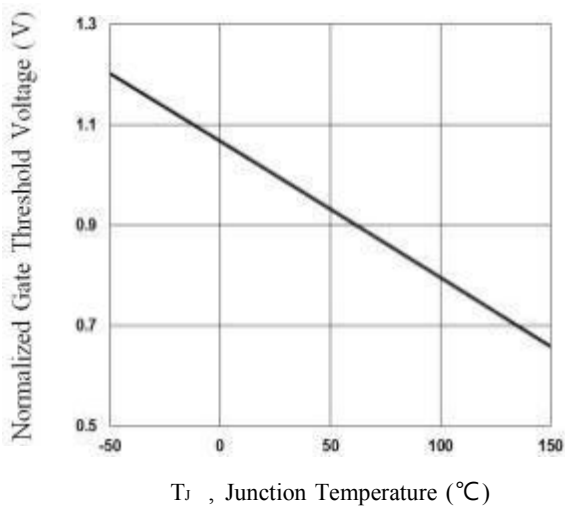


Fig. 3 Normalized V_{th} vs. T_J

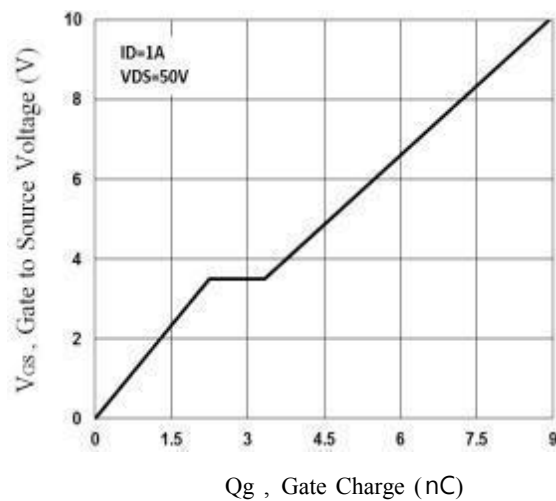


Fig. 4 Gate Charge Waveform

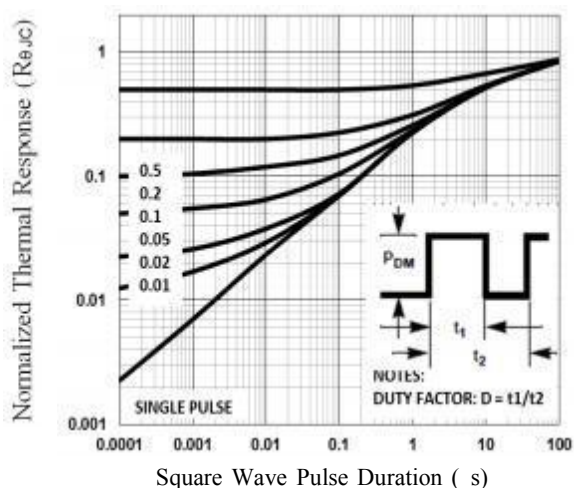


Fig. 5 Normalized Transient Impedance

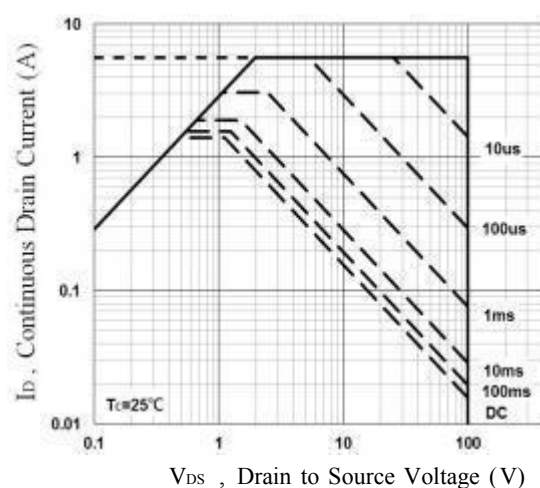


Fig. 6 Maximum Safe Operation Area

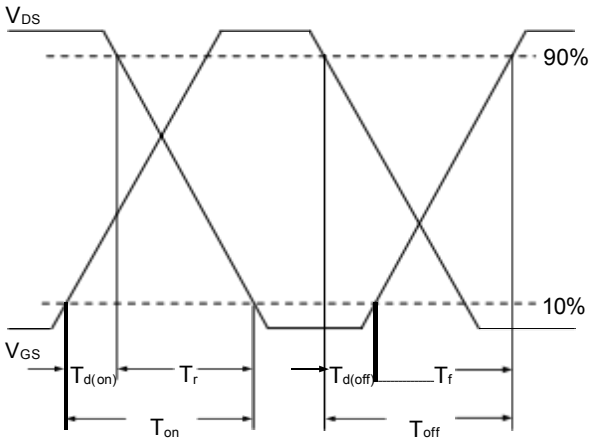


Fig. 7 Switching Time Waveform

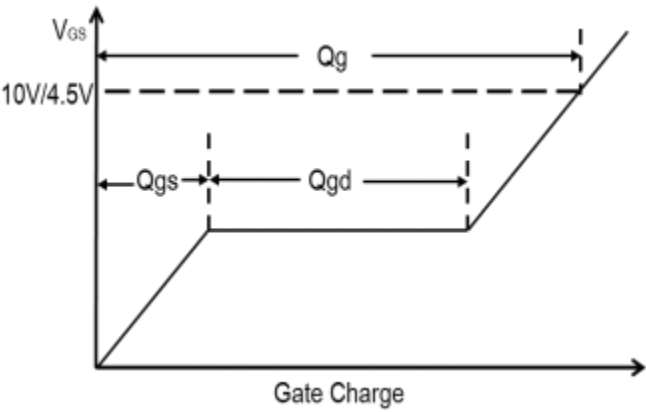
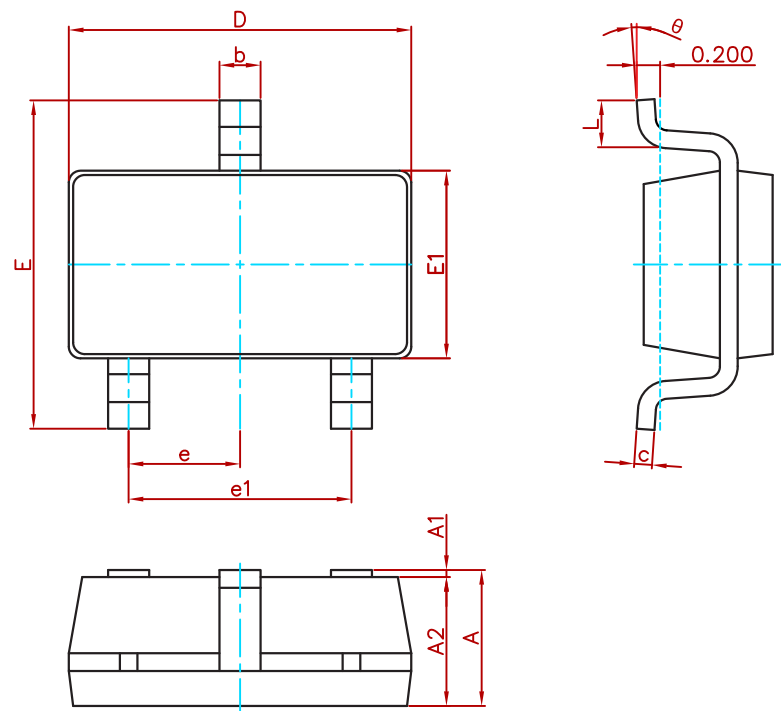


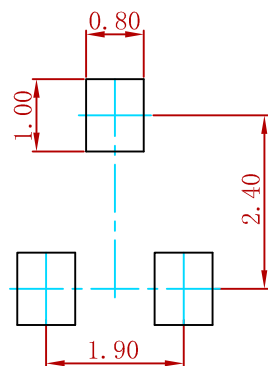
Fig. 8 Gate Charge Waveform

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3442	SOT-23-3L	3000

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